

Features

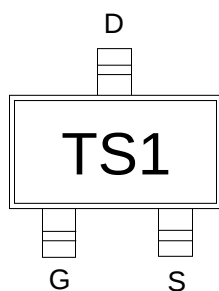
- Leading trench technology for low $R_{DS(on)}$
- Extending battery life

Product Summary

V_{DS}	$R_{DS(on)}$ TYP	I_D
-20V	75mΩ@-4.5V	-2.8A
	110mΩ@-2.5V	

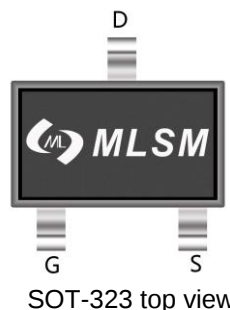
Application

- High side load switch
- Charging circuit
- Single cell battery applications such as cell phones, digital cameras ,PDAs, etc

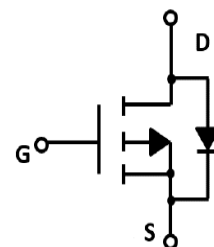


TS1: Device code

Marking and pin assignment



SOT-323 top view



Schematic diagram



Pb-Free



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V _{DS}	Drain-Source Breakdown Voltage		-20	V
V _{GS}	Gate-Source Voltage		±10	V
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	°C
I _S	Diode Continuous Forward Current	Tc=25°C	-2.8	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_C=25^{\circ}C$	-5	A
I_D	Continuous Drain Current	$T_C=25^{\circ}C$	-2.8	A
P_D	Maximum Power Dissipation	$T_C=25^{\circ}C$	0.7	W
$R_{\theta JA}$	Thermal Resistance Junction-to-Ambient		125	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLS2101W	SOT-323	TS1	3,000	45,000	180,000	7" reel

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T _J = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-20	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-20V, V _{GS} =0V	--	--	-1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±10V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-0.4	-0.62	-1.0	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-4.5V, I _D =-2.8A	--	75	100	mΩ
		V _{GS} =-2.5V, I _D =-1.0A	--	110	140	mΩ
Dynamic Electrical Characteristics @ T _J = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =-10V, V _{GS} =0V, f=1MHz	--	327	--	pF
C _{OSS}	Output Capacitance		--	62	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	55	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =-10V, I _D =-2A, V _{GS} =-4.5V	--	3.9	--	nC
Q _{gs}	Gate Source Charge		--	0.7	--	nC
Q _{gd}	Gate Drain Charge		--	0.9	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =-10V, I _D =-1A, V _{GS} =-4.5V, R _G =2.5Ω	--	6	--	nS
t _r	Turn-on Rise Time		--	30	--	nS
t _{d(off)}	Turn-Off Delay Time		--	45	--	nS
t _f	Turn-Off Fall Time		--	46	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25°C, I _S =-2A	--	--	-1.2	V

Typical Operating Characteristics

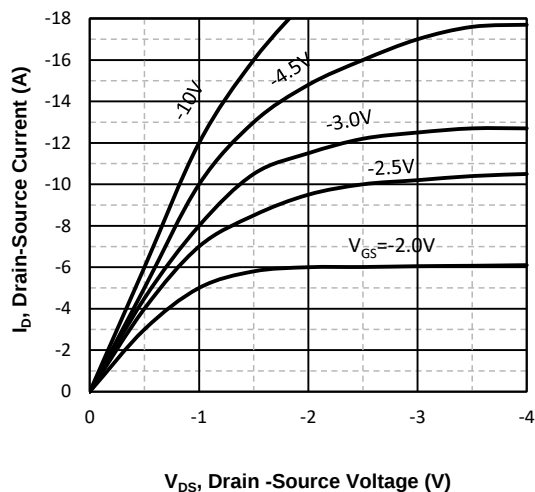


Fig1. Typical Output Characteristics

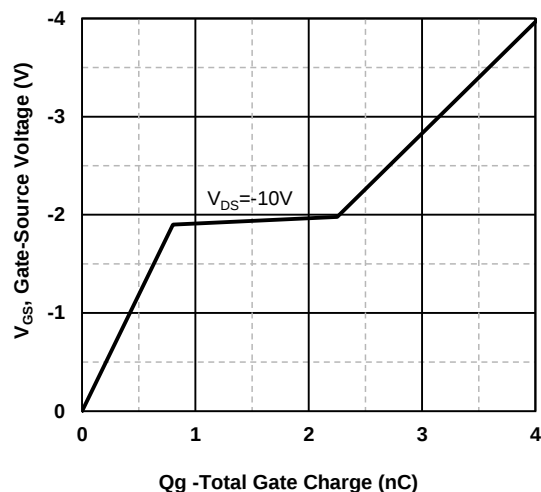


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

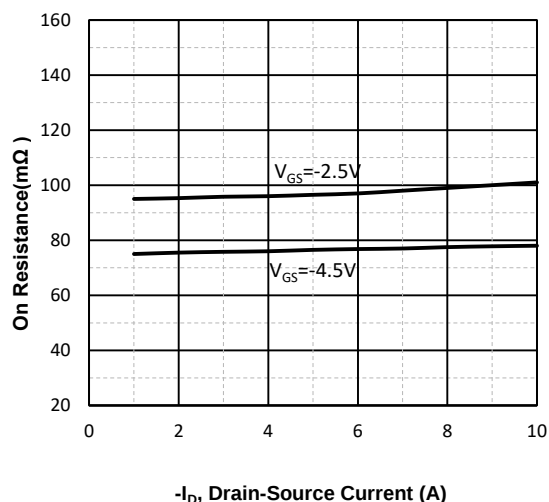


Fig3. Drain-Source on Resistance

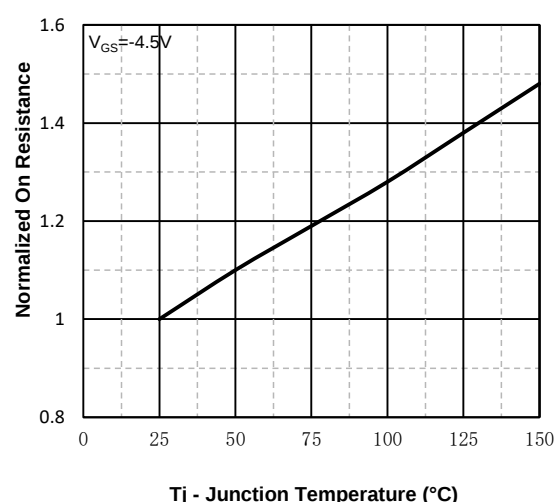


Fig4. Normalized On-Resistance Vs. Temperature

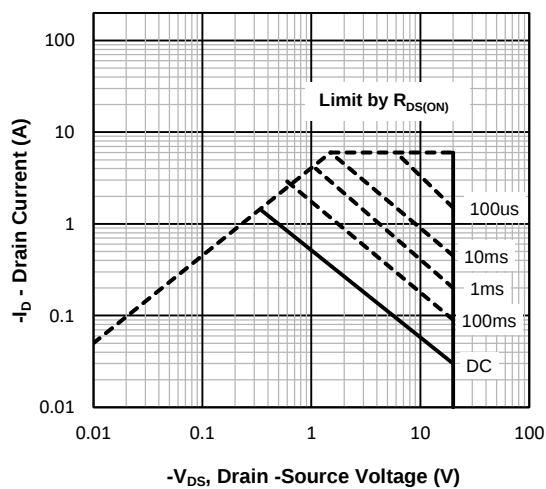


Fig5. Maximum Safe Operating Area

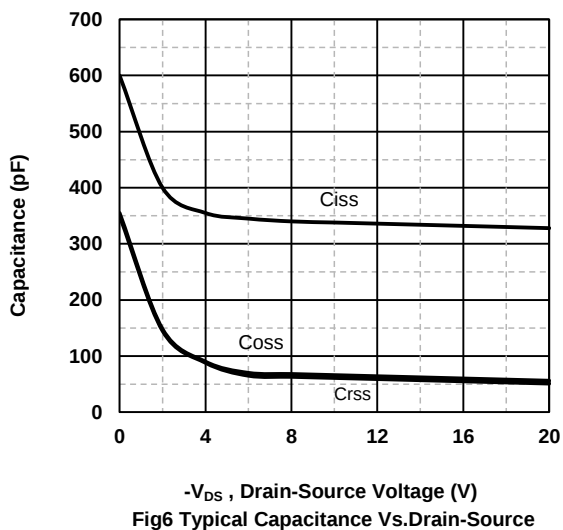
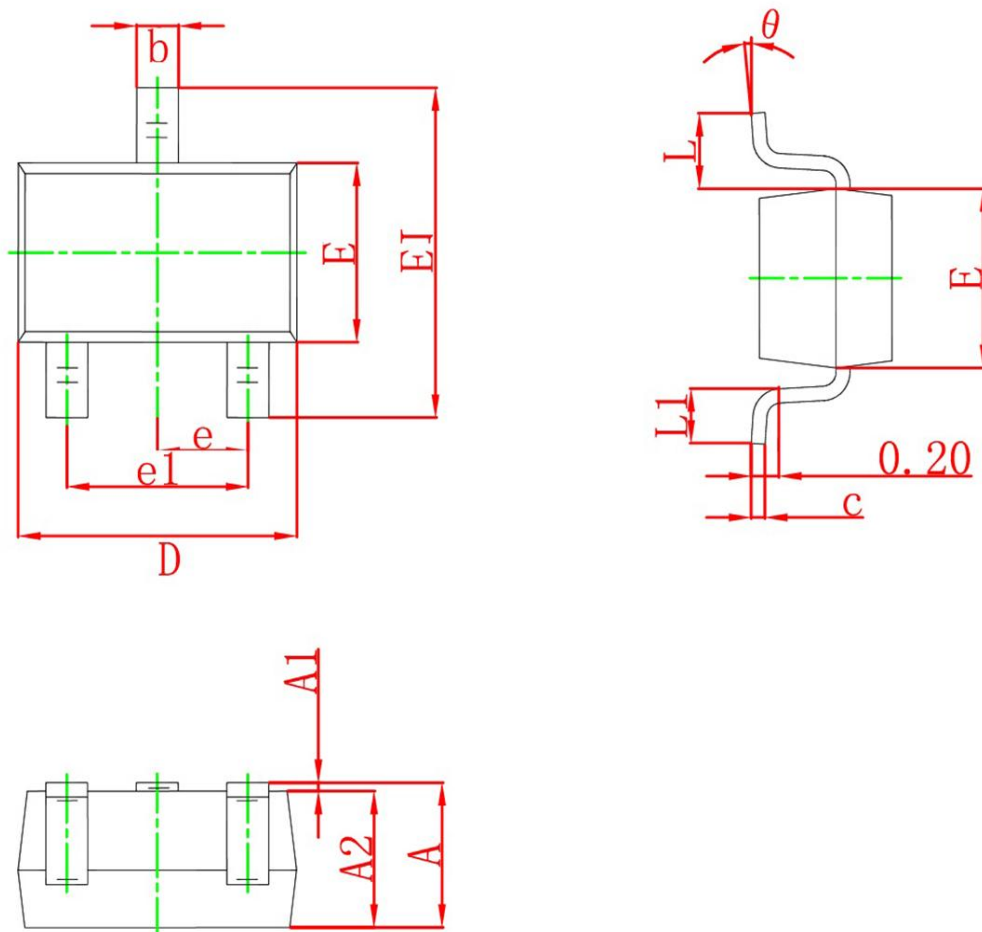


Fig6. Typical Capacitance Vs. Drain-Source

SOT-323 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650TYP		0.026TYP	
e1	1.200	1.400	0.047	0.055
L	0.525REF		0.021REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°